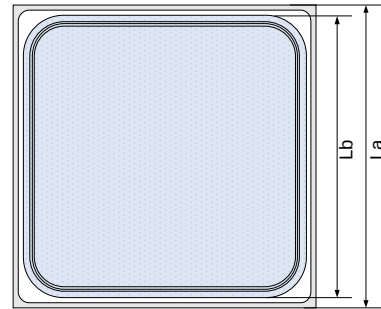


2SB083060ML SCHOTTKY BARRIER DIODE CHIPS

DESCRIPTION

- Ø 2SB083060ML is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits.;
- Ø Chip Size: 830 μ m X 830 μ m;
- Ø Chip Thickness: 280 $\pm$ 20 μ m;



Chip Topography and Dimensions

La: Chip Size: 830 μ m;

Lb: Pad Size: 670 μ m;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB083060MLYY	For axial leads package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	60	V
Average Forward Rectified Current	IFAV	1	A
Peak Forward Surge Current@8.3ms	IFSM	30	A
Maximum Operation Junction Temperature	TJ	125	°C
Storage Temperature Range	TSTG	-40~125	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=1mA	60	--	V
Forward Voltage	VF	IF=1A	--	0.70	V
Reverse Current	IR	VR=60V	--	1	mA